

NSWC Soft Switched Inverter Development Experience

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Background

- This work was funded by the Office of Naval Research under the Power Electronic Building Block Program
- The goal of the PEBB program is to enable the application of more electric power conversion for US Navy ships through the affordable implementation of advanced electrical power conversion techniques and components.

Background

- NSWEC was tasked to investigate the use of soft switching inverter technology in a multifunctional electrical power converter.
- Concurrently, ONR tasked Harris Semiconductor to team with NSWEC to produce the core building blocks comprising the converter.

Background

- Chosen topology - Auxiliary Resonant Commutated Pole (ARCP) zero voltage switching inverter
 - Navy had previously worked with GE CR&D on ARCP as a candidate for DC-AC ship service inverter module (SSIM) application under the Navy's Integrated Power System (IPS) Program.
- NSWC used the GE design as its starting point using core elements produced by Harris

Background

- ARCPs that have been built at NSWCC
 - PEBB1 - based
 - pMCTs as both main and auxiliary switches
 - IGBT main switches, pMCT auxiliary switches
 - PEBB1.5 - based
 - Non-punch-through IGBT main switches, combination of p and nMCT auxiliary switches

Background

- PEBB1 Core Devices
 - Half Bridge Module
 - pMCTs
 - npt IGBTs
 - AC Module
 - pMCT
 - Gate Drive
 - Includes Jumper for Zero Voltage Turn-on Logic for Half Bridge
 - Water Cooled Heatsink



HARRIS PRELIMINARY 180A, 1200V
AC Switch With P-Type MOS Controlled Thyristor (MCT)

January 88

Features
180A, 1200V
Low Conduction Loss
Four Quadrant Switch
Max. Surge Current Capability
800V/dt Capability
Low Gate Drive Power
100V/dt Turn-Off Capability at +100°C
Accelerated Base Plate for Easy Heat Sinking

Description
The MCT is a MOS Controlled Thyristor designed for switching current on and off by negative and positive pulsed control on an insulated MOS gate. It is designed for use in motor controls, inverters, line switches and other power switching applications. The MCT is especially suited for resonant (zero voltage or zero current) switching applications. The SCR like forward drop greatly reduces conduction power loss. MCTs allow the control of high power circuits with very small amounts of input energy. They feature the high peak current capability common to SCR type thyristors, and operate at junction temperatures up to +150°C with active switching.

Absolute Maximum Ratings: At $T_J = +25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	MAX	TYP	MIN	UNITS
Peak Off State Voltage	V_{DS}	1200			V
Continuous Cathode Current ($T_J = +80^\circ\text{C}$)	I_{CS}	150			A
Non-Reciprocating Peak Cathode Current (Note 1)	I_{CSM}	5000			A
Peak Cathode Current	I_{CP}	300			A
Gate to Anode Voltage (Continuous)	V_{GA}	+15			V
Gate to Anode Voltage (Peak)	V_{GAP}	+100			V
Rate of Change of Voltage (dV/dt)	dV/dt	10000			V/us
Rate of Change of Current	dI/dt	50000			A/us
Maximum Power Dissipation	P_T	400			W
Operating and Storage Temperature	T_J, T_{STG}	-40 to +150			$^\circ\text{C}$
Maximum Temperature for Soldering	T_s	230			$^\circ\text{C}$

NOTE:
1. Maximum Pulse Width of 300us (Half Sine) assume T_J (Initial) = +80°C and T_J (Final) = T_J (Max) = +150°C

Electrical Specifications: At $T_J = +25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Peak On State	I_{ON}	$V_{GS} = +1200V$ $V_{DS} = +10V$ $T_J = +25^\circ\text{C}$	—	—	2.0	mA
Blocking Current	I_{BS}	$V_{GS} = +10V$ $V_{DS} = +1200V$ $T_J = +150^\circ\text{C}$	—	—	200	μA
On State Voltage	V_{DS}	$V_{GS} = +10V$ $I_{CS} = 150A$ $T_J = +25^\circ\text{C}$	—	1.8	2.0	V
Gate to Anode Leakage Current	I_{GAS}	$V_{GA} = +15V$ $T_J = +25^\circ\text{C}$	—	1.0	2.0	nA
Gate to Anode Capacitance	C_{GAS}	Per MCT	—	40	—	pF
Gate Amplifier Input Charge	Q_{GI}	Per MCT	—	150	—	nC
Thermal Impedance	R_{JA}	Per MCT	0.12	—	0.15	$^\circ\text{C/W}$
Amplifier to Case	R_{JC}	Per Diode	0.15	—	0.20	$^\circ\text{C/W}$
Diode Forward Drop	V_D	$V_{GS} = +10V$ $I_{CS} = 150A$ $T_J = +25^\circ\text{C}$	—	2.0	2.5	V
Reverse Recovery Current	I_{RR}	$V_{GS} = +120V$, $V_{DS} = +110V$ $T_J = +25^\circ\text{C}$	—	30	—	A
Voltage Over-Shift	V_{OS}	$V_{GS} = 300V$, $dV/dt = 150A/us$ $T_J = +25^\circ\text{C}$	—	100	—	V
Power Dissipation	P_T	Continuous, $T_J = +25^\circ\text{C}$, $R_{JA} = 0.12^\circ\text{C/W}$	—	400	—	W

Recommended Gate Voltage Rise Rate (dV/dt) from 0V to +100V is less than 200V/us

Caution: Preliminary Data. Data shown is subject to change.

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Background

- PEBB1.5 Core Devices
 - Half Bridge Module
 - npt IGBTs
 - AC Module
 - one pMCT one nMCT
 - snubber resistor
 - Gate Drives
 - Heat Sink Assembly



HARRIS
MICROELECTRONICS

February-98

Features
 150A, 1200V
 5kA Surge Current Capability
 80kA/μS di/dt Capability
 Low Conduction Loss
 Low Gate Drive Power
 300A Gate Turn-Off Capability at +150°C
 Isolated Base Plate with Copper Sponge for Easy Heat Sinking
 Temperature Sensor

Description
 The MCT is a MOS Controlled Thyristor designed for switching current on and off by negative and positive pulsed control on an insulated MOS gate. It is designed for use in motor controls, inverters, line switches and other power switching applications. The MCT is especially suited for resonant (zero voltage or zero current switching) applications. The SCR like forward drop greatly reduces conduction power loss. MCTs allow the control of high power circuits with very small amounts of input energy. They feature the high peak current capability common to SCR type thyristors, and operate at junction temperature up to +150°C with active switching.

Absolute Maximum Ratings At $T_c = +25^\circ\text{C}$, Unless Otherwise Specified

Peak Off State Voltage.....

PRELIMINARY

150A, 1200V

AC Switch With P&N Type MOS Controlled Thyristor (MCT)

PACKAGE SIZE 4" X 3" x 1.25"
 1 P-MCT & 1 N-MCT S-8 (1cm²) & 2 S-7 DIODES (0.6cm²)

PEBB1.5 AC Switch Module

SYMBOL

A.C. SWITCH

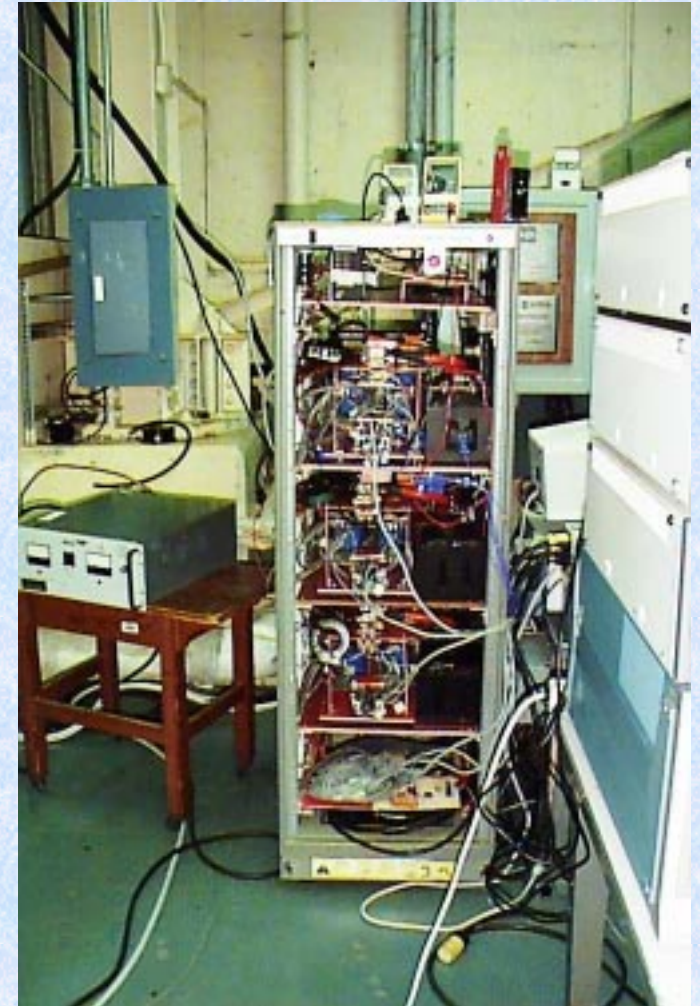
SYMBOL	UNITS
V_{DRM}	+/-1200 V
	A
	A
	A
	V
	V
	V/μs
	V/μs
	W
	W
	°C
	°C
	UNITS
	μA
	μA
	μA
	μA
	V
	V
	V
	V
	nA
	nF
	nC
	C/W
	C/W
	A
	V
	μS
	mJ

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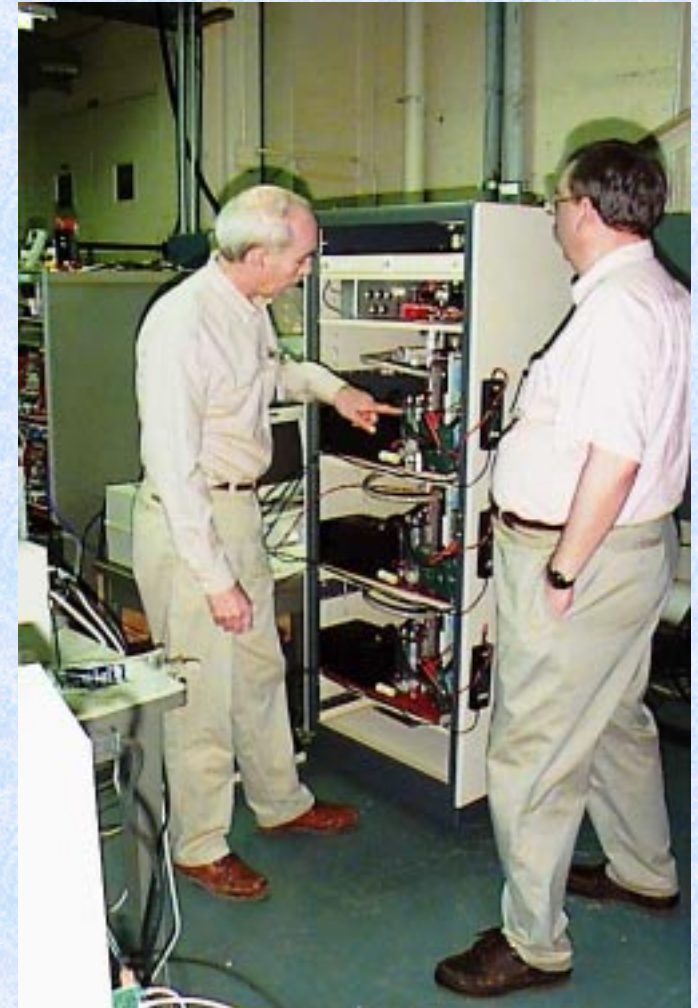
PEBB 1 Hardware

- Qty of 4 three phase units
 - Main switch - PMCT
 - Aux Switch - PMCT
 - DC Bus Caps - orig. 7000uF
 - reduced to 3500uF per phase
 - Resonant inductor - 1.6uH
 - Resonant Cap - .8uf per switch
 - 1.6uf total per phase
 - Resonant frequency ~ 100kHz
 - Output filter - 175uH, 50uF
 - Controller TMS320 DSP
 - 100ns step control of ac switch on time
 - at 800vdc = 40 amp step control



PEBB 1.5 ARCP Inverter

- Design Specifications: DC-AC operating mode
 - Input: 750 - 850Vdc
 - Output: 450Vac RMS at 250kW (water cooled)
- Major Components
 - Main switch - NonPunchThrough IGBT
 - Aux. Switch - Combo N-and P-MCT
 - DC Bus Caps - 6900 uF per phase
 - Resonant inductor - 1.0-1.2 uH
 - Resonant Cap - .1 uF/switch, .2uF/phase
 - DSP Based Digital Controller
 - 100ns step control of ac switch on time
 - at 800vdc = 40 amp step control
- Present status
 - Assembly completed 4/3/98
 - Tested up to 200kW 10/98



Perceived Benefits of ARCP

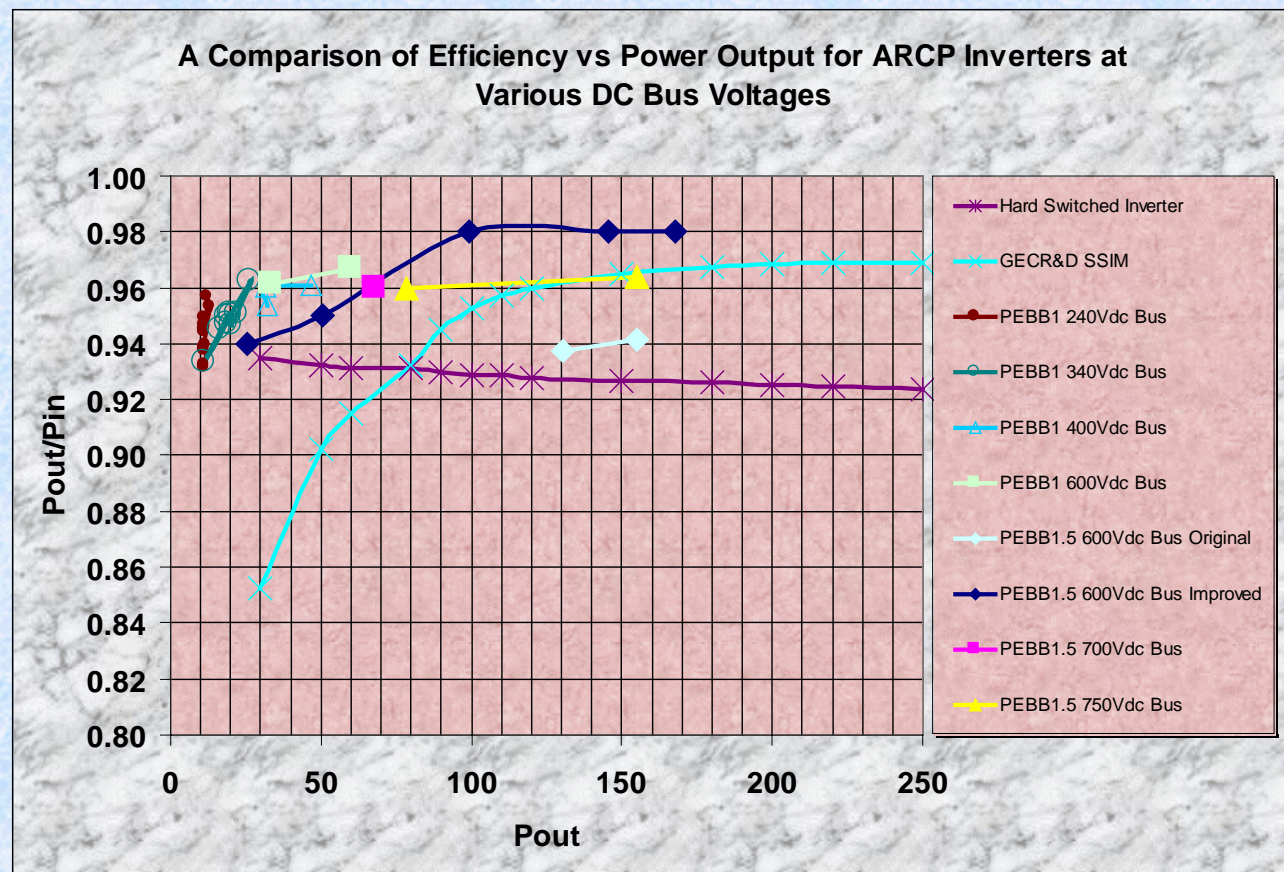
- Lower Loss/Higher Efficiency
- Lower Device Stress, Lower High Frequency EMI, Friendlier to the load in terms of dV/dt and dI/dt

Perceived Benefits of ARCP

- Lower Loss/Higher Efficiency
 - An ARCP inverter was designed built and tested by PSU under NSWC PEBB contract to investigate high frequency converter issues
 - IGBT Main switches/FET auxiliary
 - ARCP operation 190V, 14A output - 63.4 kHz switching frequency
 - Disabled auxiliary circuit and operated as hard switched inverter at same output voltage and current
 - Switching frequency slowly increased until failure occurring at 32.5kHz
 - [1] Salberta, Frederick; Mayer, Jeffrey S.; and Cooley, Roger T., “An improved Control Strategy for a 50kHz Auxiliary Resonant Commutated Pole Converter,”Power Electronics Specialist Conference St Louis MO June 22-27th 1997

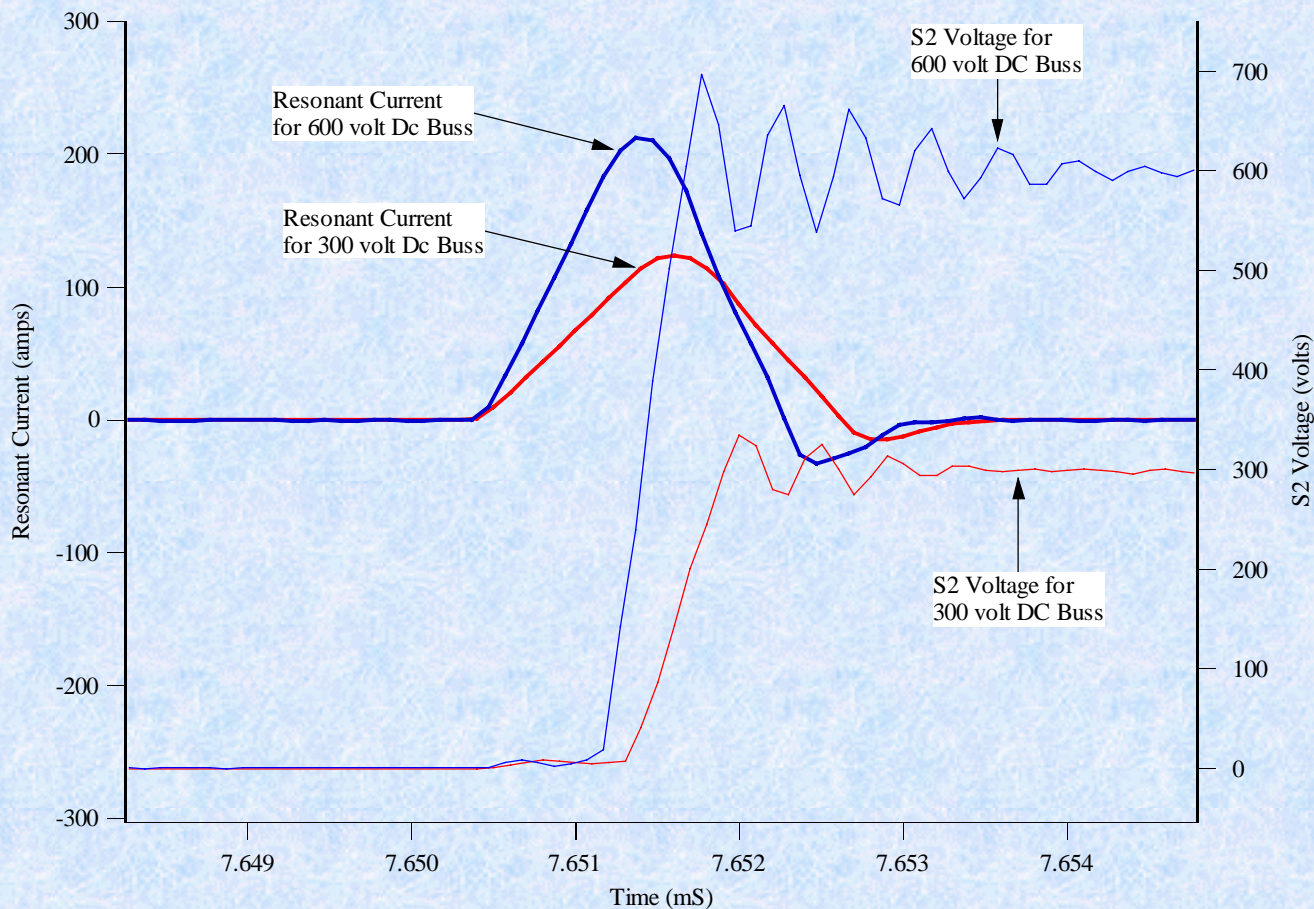
Perceived Benefits of ARCP

- Lower Loss/Higher Efficiency
- [2] Keraluwala, Mustansir; Szczesny Paul; Esser, Albert and Hegner, Henry, “Development of a 250kVA, High Performance, Ship Service Inverter Module (SSIM) for Future Naval Applications,” Power Electronics Applications –PEBB Workshop November 5 1997



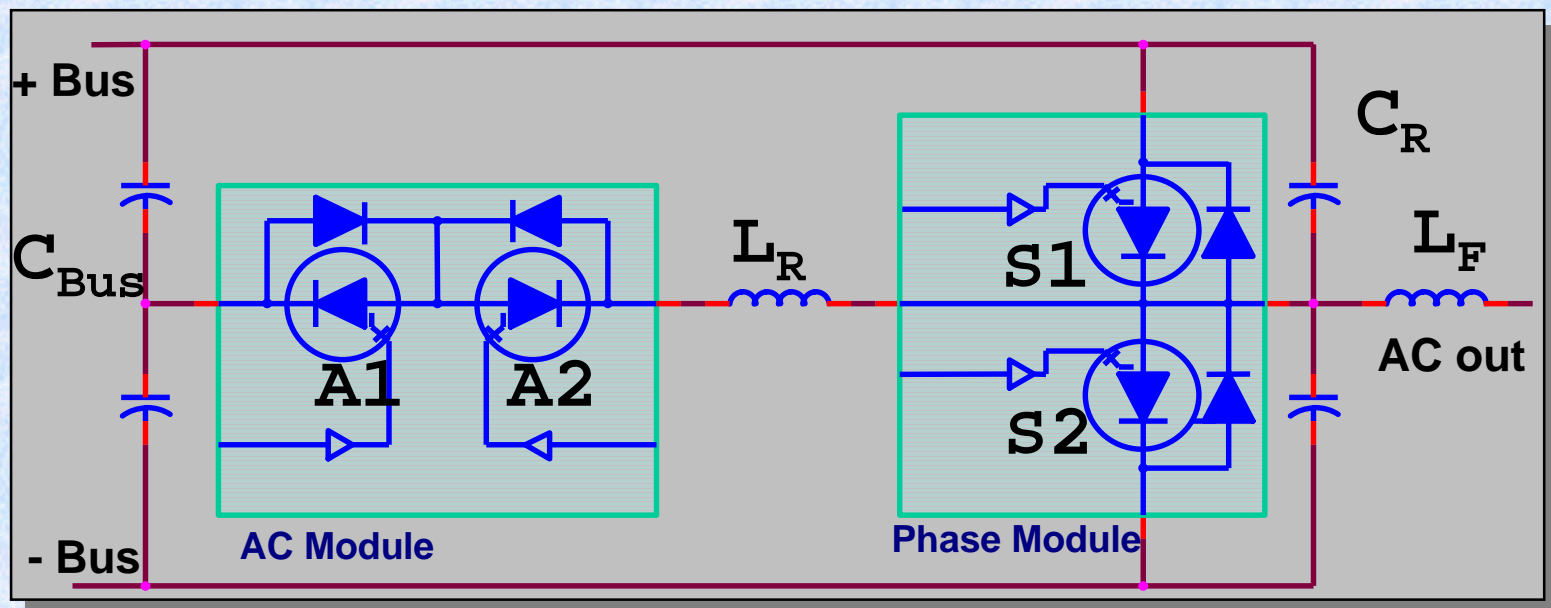
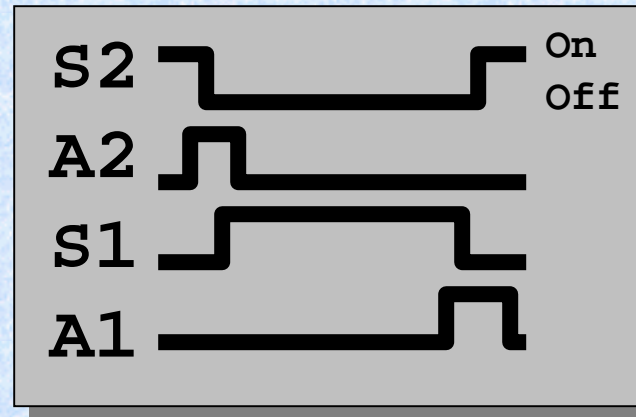
Perceived Benefits of ARCP

- Lower Device Stress, Lower High Frequency EMI, Friendlier to the load in terms of dV/dt and dI/dt



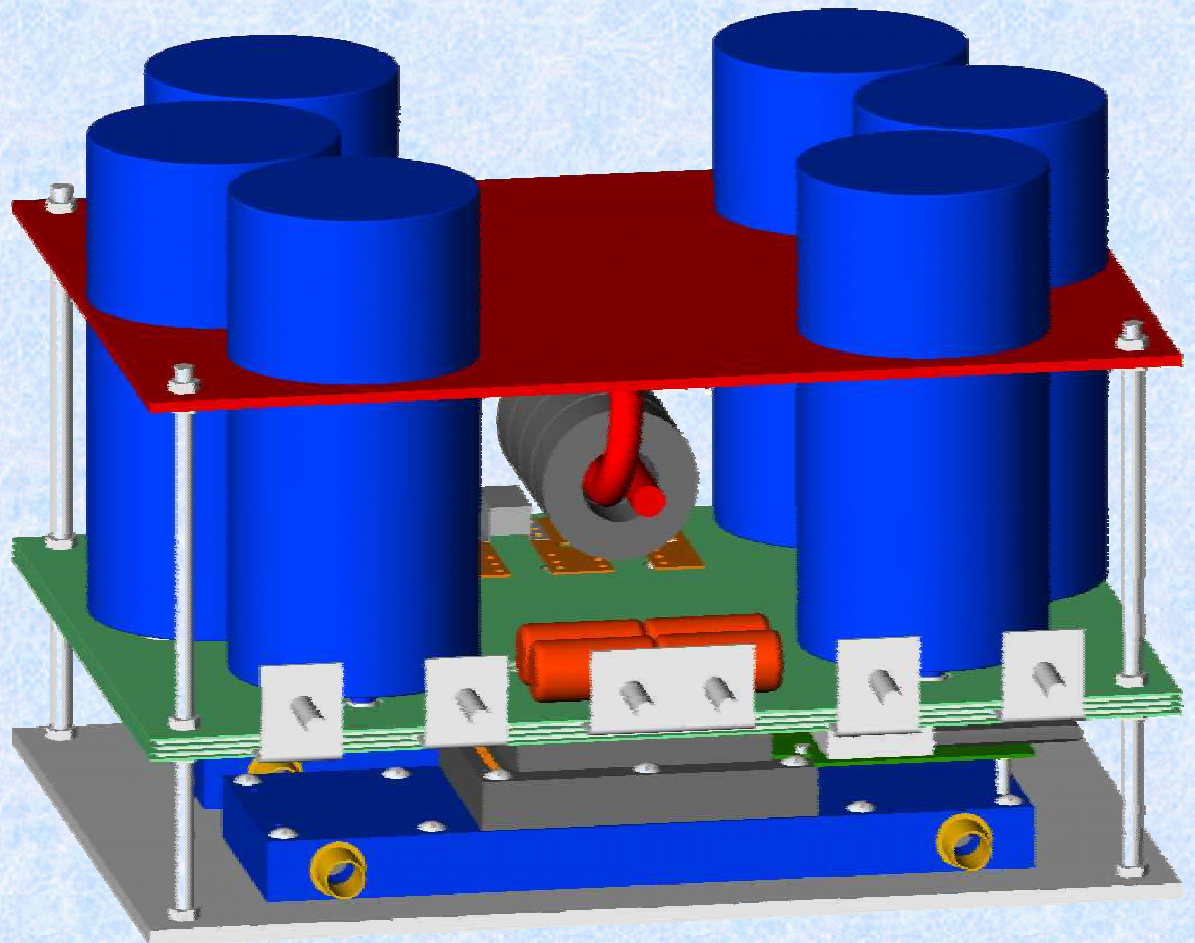
Perceived Tradeoffs

- Higher parts count
- Controller Complexity
- Higher cost



Perceived Tradeoffs

- Higher parts count
 - DC bus cap function
 - supply resonant current pulses (soft switching only)
 - supply HF ripple demanded by PWM (hard switch demand may be worse than soft switch due to the shape of the demanded voltage waveform -square wave vs trapezoid)
 - could end up being a wash



Perceived Tradeoffs

- Parts Count - Resonant Inductor
 - L value relatively low $\sim 1.0 - 1.5\mu\text{H}$
 - High frequency current components
 - Litz wire used
 - L value subject to variability in manufacture
 - L value subject to variability under operation due to temperature fluctuations (this has not yet been measured)
 - Not having a stable value inductor limits how close controller can push safety margins



Perceived Tradeoffs

- Parts Count - Resonant Capacitor
 - Requires accurate known value with little or no temperature drift
 - Quantity needed dependent on tail current of Phase switch
 - Expensive



NPO Dielectric General Specifications



NPO is the most popular formulation of the "temperature-compensating," EIA Class I ceramic materials. Modern NPO formulations contain neodymium, samarium and other rare earth oxides.

NPO ceramics offer one of the most stable capacitor dielectrics available. Capacitance change with temperature is $0 \pm 30 \text{ ppm}/^\circ\text{C}$ which is less than $\pm 0.3\% \Delta C$ from -55°C to $+125^\circ\text{C}$. Capacitance drift or hysteresis for NPO ceramics is negligible at less than $\pm 0.05\%$ versus up to $\pm 2\%$ for films. Typical capacitance change with life is less than $\pm 0.1\%$ for NPOs, one-fifth that shown by most other dielectrics. NPO formulations show no aging characteristics.

The NPO formulation usually has a "Q" in excess of 1000 and shows little capacitance or "Q" changes with frequency. Their dielectric absorption is typically less than 0.6% which is similar to mica and most films.

Part Number (see page 3 for complete information and options)

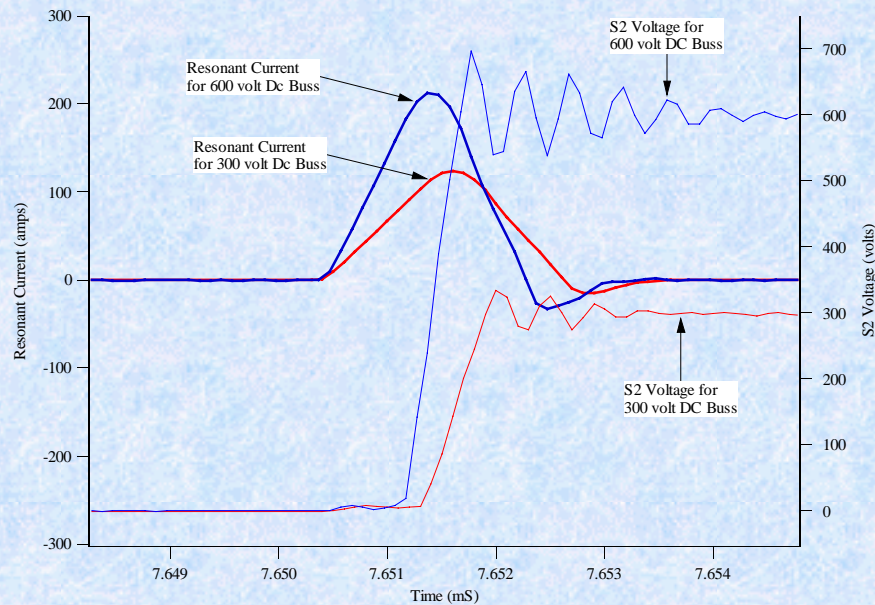
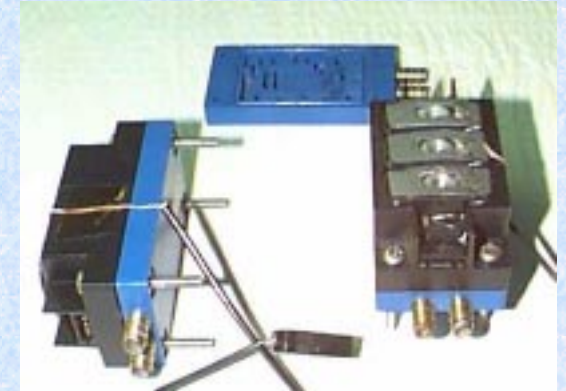
0805	5	A	101	K	A	T	2	A
Size (L" x W")	Voltage 50V = 5 100V = 1 200V = 2	Dielectric NPO = A	Capacitance Code	Capacitance Tolerance Preferred K = $\pm 10\%$ J = $\pm 5\%$	Failure Rate	Termination T = Plated Ni and Solder	Marking Packaging 2 = 7" Reel Paper/Unmarked	Special Code A = Std. Product

Performance Characteristics: NPO

Capacitance Range	0.5 pF to .033 μF (1.0 $\pm 0.2 V_{rms}$, 1kHz, for $\leq 100 \text{ pF}$ use 1 MHz)
Capacitance Tolerances	Preferred $\pm 5\%$, $\pm 10\%$ others available: $\pm 25 \text{ pF}$, $\pm 5 \text{ pF}$, $\pm 1\%$ ($\geq 25 \text{ pF}$), $\pm 2\%$ ($\geq 13 \text{ pF}$), $\pm 20\%$ For values $\leq 10 \text{ pF}$ preferred tolerance is $\pm 5 \text{ pF}$, also available $\pm 25 \text{ pF}$.
Operating Temperature Range	-55°C to $+125^\circ\text{C}$
Temperature Characteristic	$0 \pm 30 \text{ ppm}/^\circ\text{C}$
Voltage Ratings	25, 50, 100 & 200 VDC ($+125^\circ\text{C}$)
Dissipation Factor and "Q"	For values $> 30 \text{ pF}$: 0.1% max. ($+25^\circ\text{C}$ and $+125^\circ\text{C}$) For values $\leq 30 \text{ pF}$: "Q" = $400 + 20XC$ (C in pF)
Insulation Resistance ($+25^\circ\text{C}$, RVDC)	100,000 megohms min. or 1000 M Ω - μF min., whichever is less
Insulation Resistance ($+125^\circ\text{C}$, RVDC)	10,000 megohms min. or 100 M Ω - μF min., whichever is less
Dielectric Strength	250% of rated voltage for 5 seconds at 50 mamp max. current
Test Voltage	$1 \pm 0.2 V_{rms}$
Test Frequency	For values $\leq 100 \text{ pF}$: 1 MHz For values $> 100 \text{ pF}$: 1 KHz

Perceived Tradeoffs

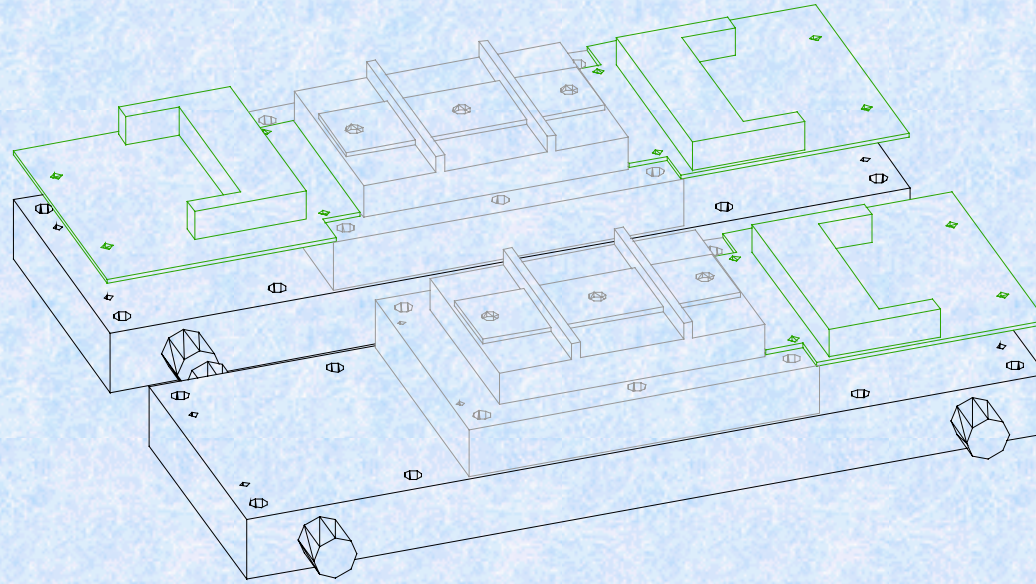
- Parts Count - Auxiliary switch
 - needs to supply very high di/dt pulse
 - zero current turn off
 - PEBB1 and PEBB1.5 variants



Perceived Tradeoffs

- Parts Count - feedback signals needed
 - Soft Switch Transition
 - V_{dc} - low bandwidth, 1% resolution
 - I_{output} - 3 samples within 120 degrees of switching frequency, 12 bit resolution
 - Voltage Regulation
 - V_{out} - update at switching frequency, 1% resolution

Perceived Tradeoffs

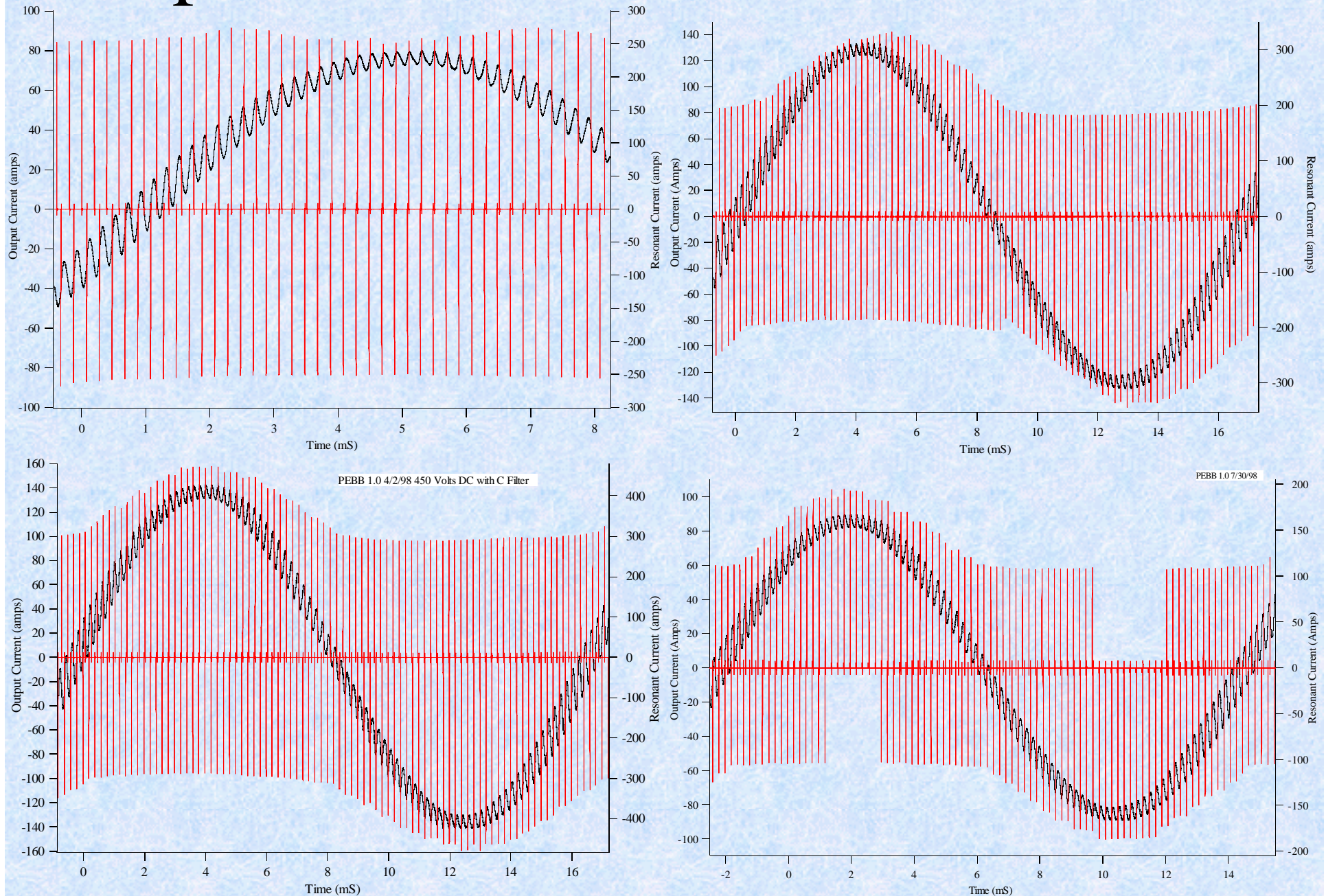


- Higher cost
 - The goal of the PEBB program is to develop an automated manufacturing process using pick and place assembly techniques to produce a module employing the proper types of semiconductor switches, diodes and ultimately passive and control components interconnected in the circuit topology requested by the circuit designer
 - Harris PEBB1.5 modules employing HTP semiconductor die in a generic, user definable arrangement begin to demonstrate a way of removing the costly hand assembly process from power converter manufacturing

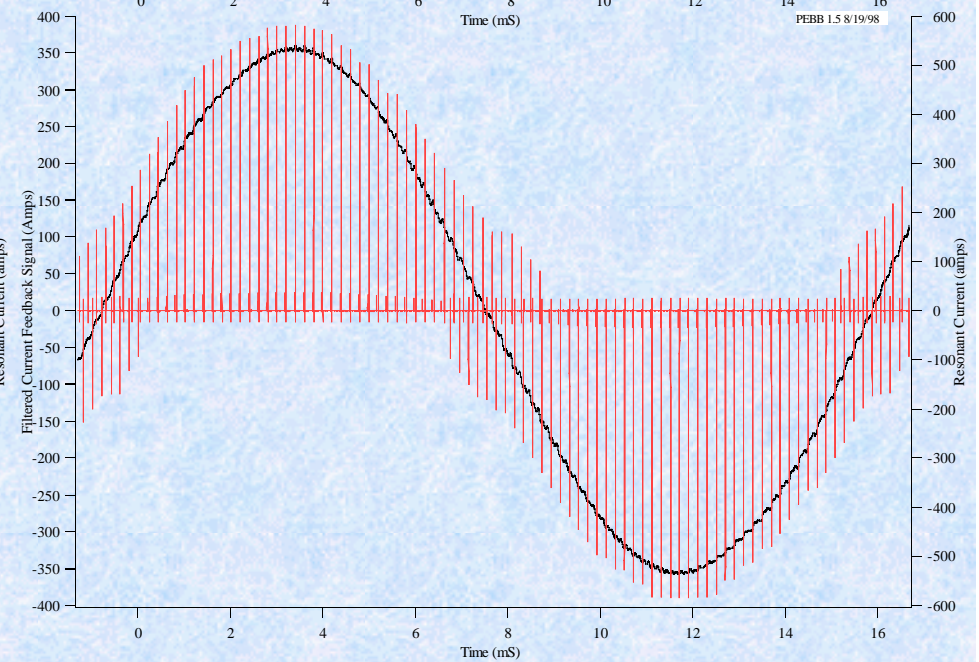
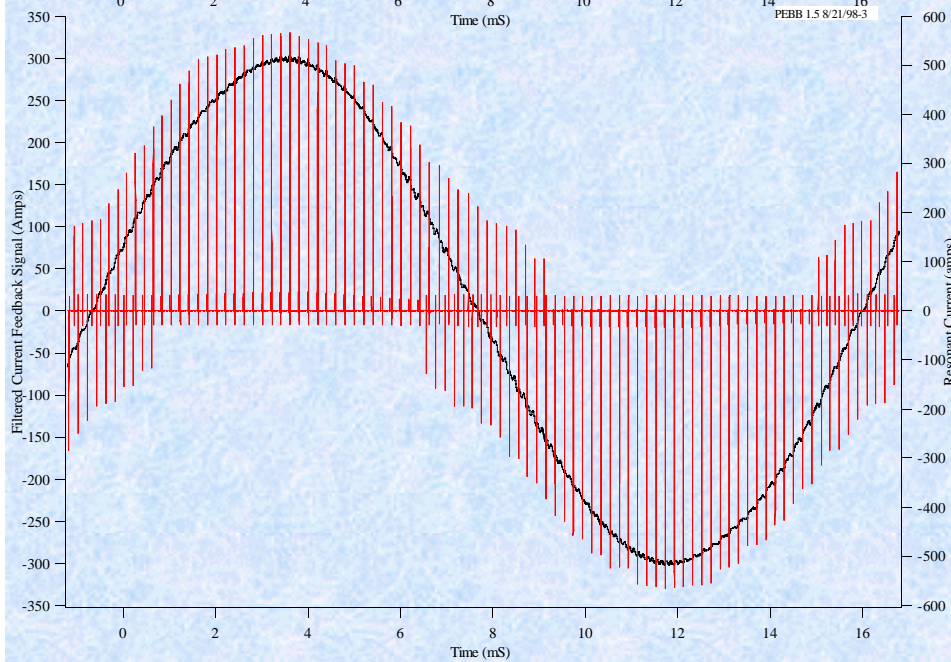
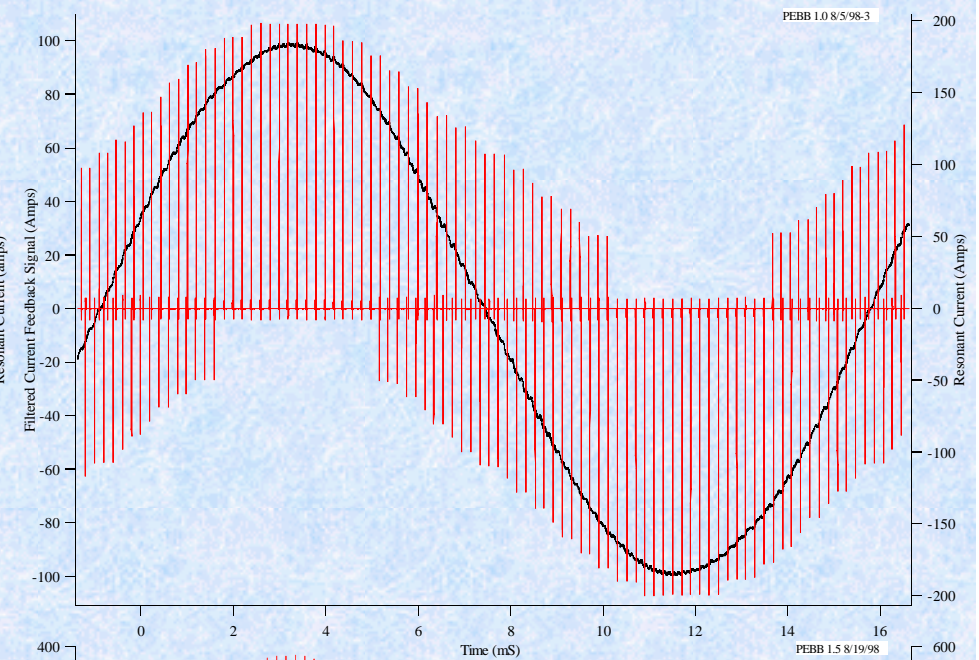
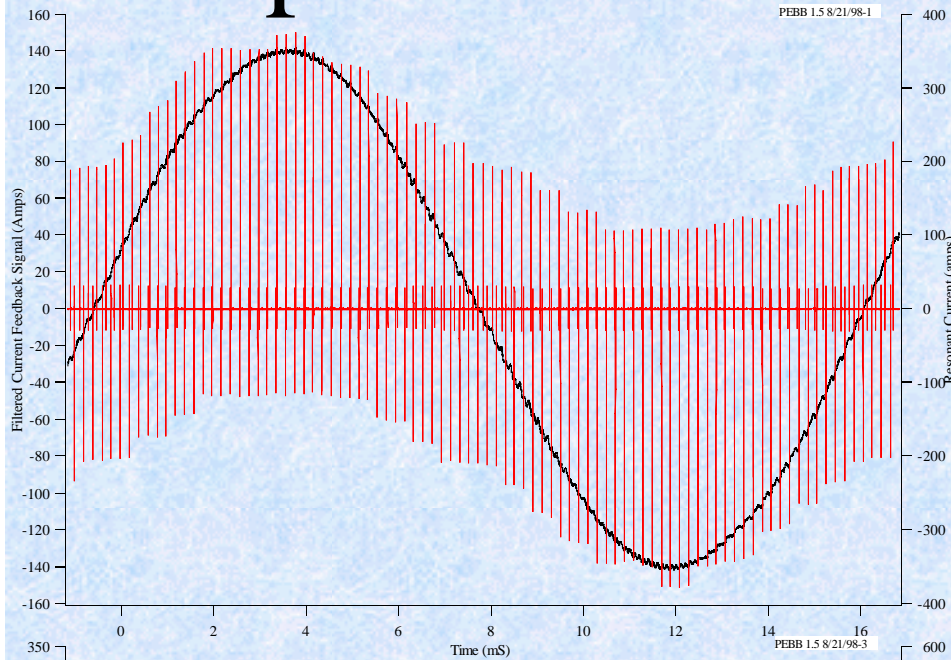
Perceived Tradeoffs

- A significant amount of effort was made in order to minimize the cost and size impact of the additional components required for ARCP
- The key was to supply the minimum amount of resonant energy to allow a zero voltage transition to occur
- This would minimize the current handling requirements of the additional components

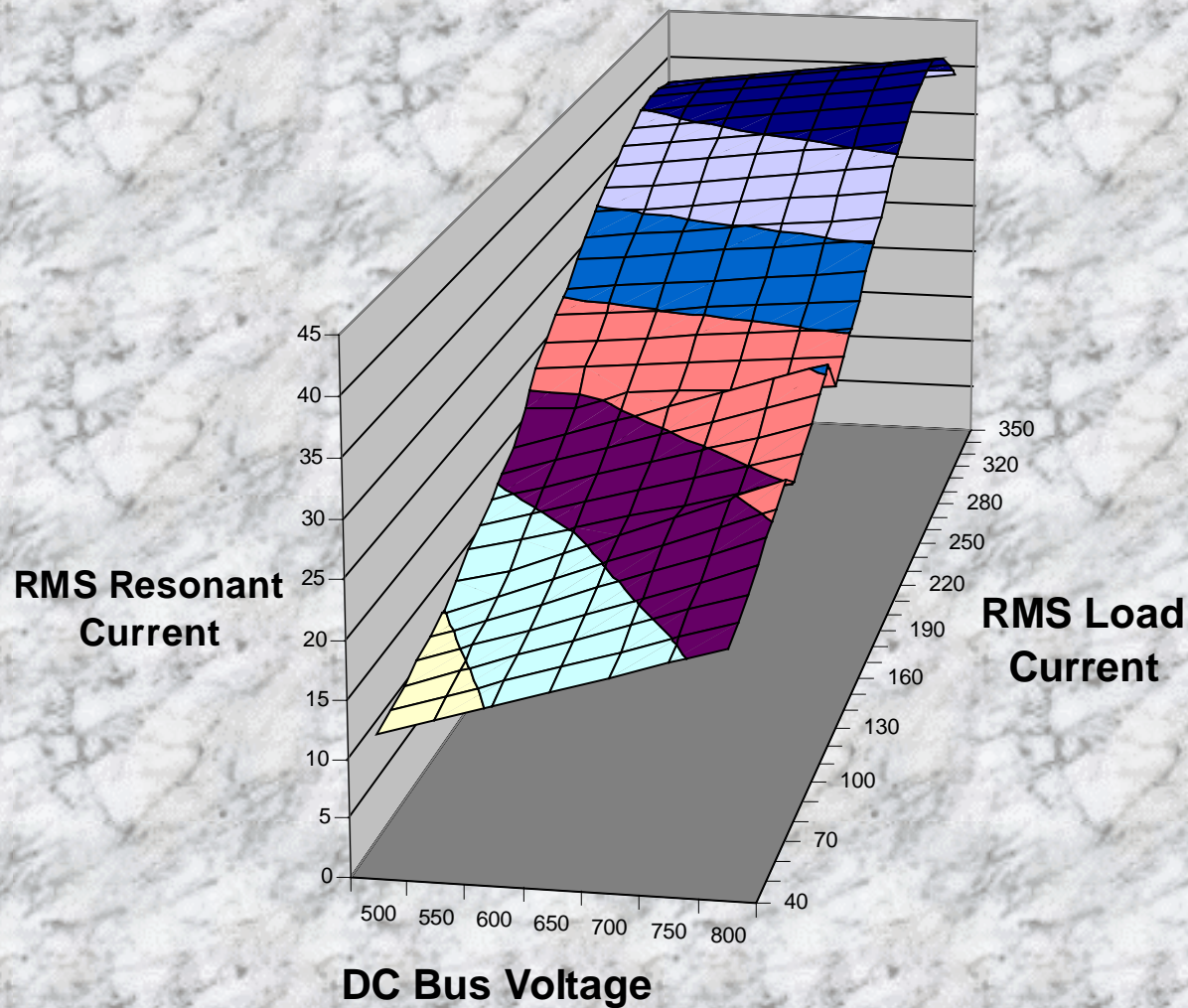
Steps to Minimize Resonant Current



Steps to Minimize Resonant Current



Surface Plot of I_{res} vs V_{dc} and I_{Load}



Projects to approximately 50A rms resonant current for full 250kW

Issues uncovered during analysis and testing

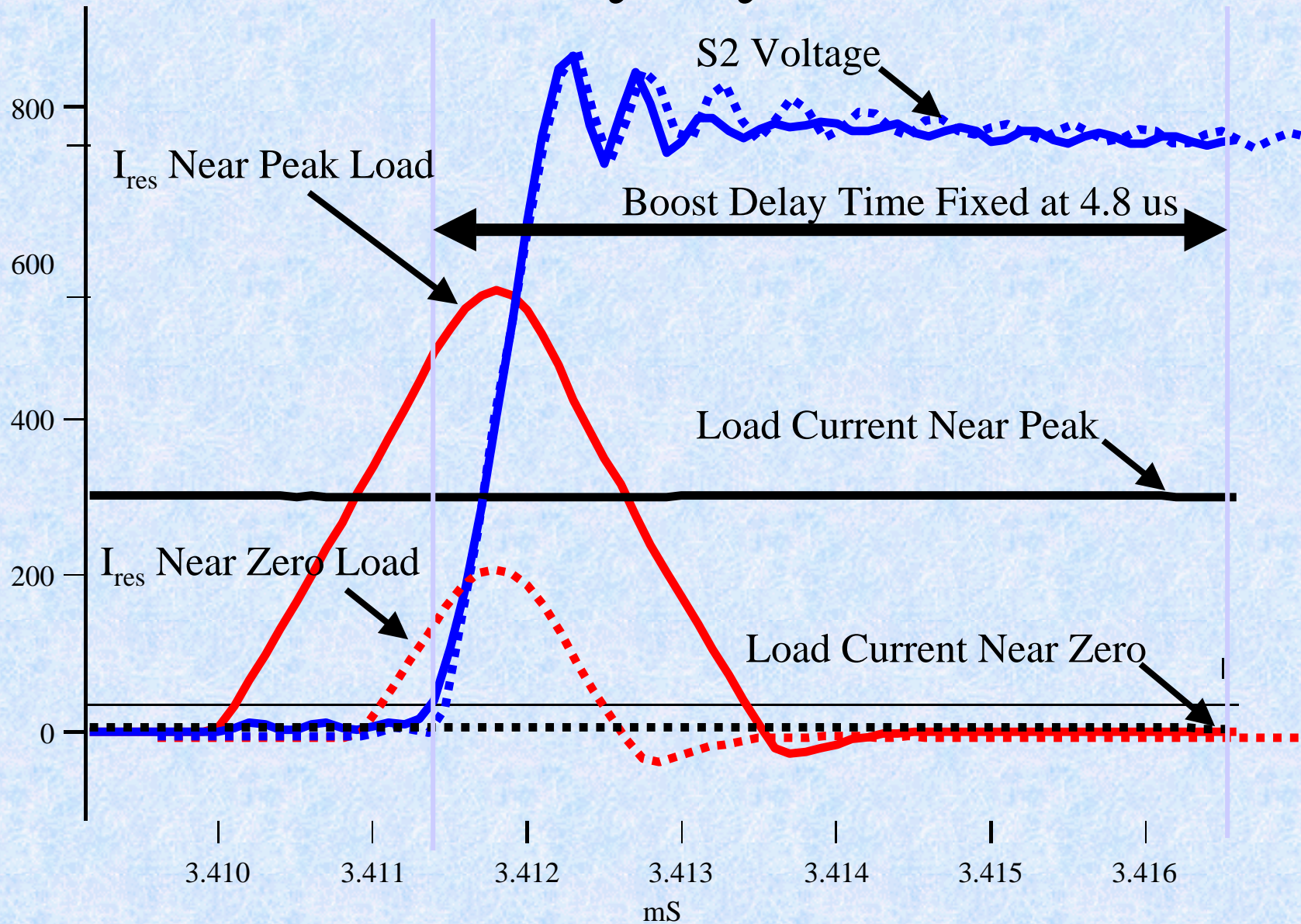
- Output filter design and manufacturing
 - hard to find inexpensive, compact, high frequency, high power inductors



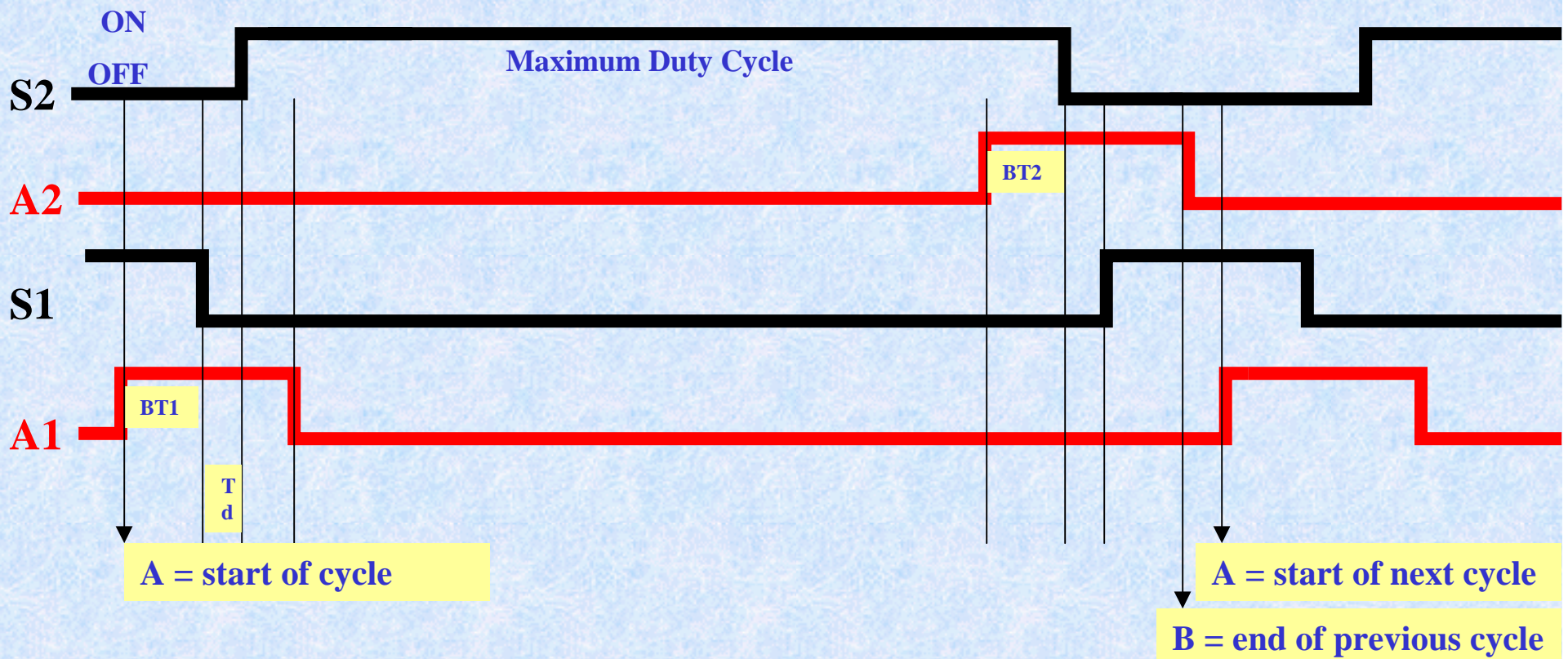
Issues uncovered during analysis and testing

- Present Controller Implementation has data sampling latency times which compromise performance
- Loss of duty cycle due to resonant pulse times and above latency times
- Difficult to design into controller enough safety margins to operate within real world limitations of chosen devices, yet have enough performance to compete with a hard switched converter

Maximum Duty Cycle Limitation



Maximum Duty Cycle Limitation



Event "A" Cannot happen until event "B" occurs

Event "B" cannot complete until resonant current pulse = 0

That time is not readily known, so a worst case Boost delay time of 4.8 μ s is used

Maximum Duty Cycle Limitation

$$V_{LL} = 0.612 * V_{dc} [2d_{\max} - 1]$$

- It is estimated that next generation controller will enable reducing latencies and dead times by up to 5us.
- A 10% improvement in duty cycle utilization corresponds to a 20% improvement in available Line to Line Voltage
- Note: Third Harmonic Injection will increase V_{LL} by 15%

Conclusion

- The NSWEC PEBB as presently implemented as an ARCP inverter has been demonstrated at 200kW.
- On-going refinements are continuing, which allow the ARCP to achieve higher performance and multiple power conversion functions.

Conclusion

- The areas where improvements can be made to narrow the gap are:
 - A method of partitioning ARCP-specific control circuitry as close to the phaseleg as possible in order to allow traditional controllers to be employed
 - An automated module assembly process that would allow the ARCP to be easily manufactured with minimal hand assembly
 - less expensive high performance capacitors and inductors